

*Cunk A*  
on said second well, said first conductive layer electrically connecting said first well and said second well; and

a first contact electrically connected with said first well.

*AS Sub C*  
5. (Amended) A semiconductor device according to claim 1, further comprising:  
a second conductive layer formed in said surface of said semiconductor substrate and provided on said first well without being in contact with said second well, wherein said first contact is in contact with said second conductive layer.

Please add new claims 11-14 as follows:

*Ag Sub C*  
11. (New) The semiconductor device according to claim 1, wherein the first and second semiconductor elements are first and second transistors respectively.

*B Sub C*  
12. (New) The semiconductor device according to claim 5, wherein said second well is deeper than said first well.

13. (New) A semiconductor device comprising:

*Sub C*  
a semiconductor substrate;  
a first well of a prescribed conductivity type selectively formed in a surface of said semiconductor substrate;

*B Sub C*  
a second well of the same conductivity type as said prescribed conductivity type selectively formed in a surface of said semiconductor substrate;

a conductive layer across said first well and said second well in said surface of said semiconductor substrate with an end provided on said first well and another end provided on said second well, said conductive layer including a compound layer of the material for said semiconductor substrate and a metal; and

a first contact electrically connected with said first well.

*Sub C*  
14. (New) The semiconductor device according to claim 13, wherein said conductive